MA123

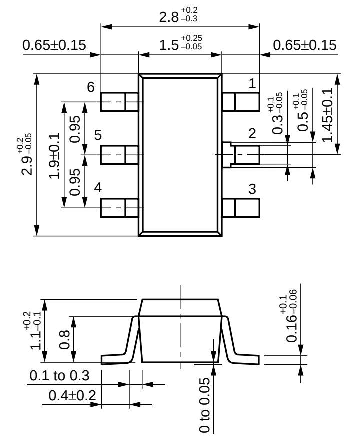
Silicon epitaxial planer type

For switching circuits

■ Features

- Four-element incorporated in one package, enabling high-density mounting
- Point-symmetrical wiring, without need of taping direction
- Short reverse recovery period t_{rr}
- Small capacity between pins, C_t

Unit : mm



1 : Anode 1
2 : Anode 2
3 : Cathode 3, 4
4 : Anode 3
5 : Anode 4
6 : Cathode 1, 2

Mini Type Package (6-pin)

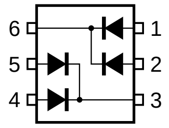
Marking Symbol : M2B

■ Absolute Maximum Ratings (Ta= 25˚C)

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	80	V
Peak reverse voltage	V_{RM}	80	V
Forward current (DC)	I_F	❋100	mA
Peak forward current	I_{FM}	❋225	mA
Non-repetitive peak forward surge current	I_{FSM} *	❋500	mA
Junction temperature	T_j	150	˚C
Storage temperature	T_{stg}	– 55 to +150	˚C

❋ Value in single diode used
* t=1s

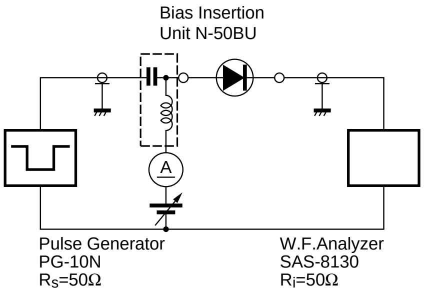
■ Internal Connection

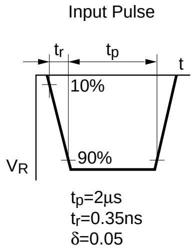


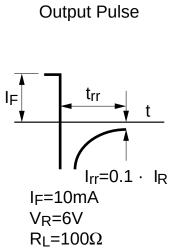
■ Electrical Characteristics (Ta= 25˚C)

Parameter	Symbol	Condition	min	typ	max	Unit
Reverse current (DC)	I_R	V_R= 75V			100	nA
Forward voltage (DC)	V_F	I_F=100mA			1.2	V
Reverse voltage (DC)	V_R	I_R=100µA	80			V
Terminal capacitance	C_t	V_R= 0V, f=1MHz			2	pF
Reverse recovery time	t_{rr} *	I_F=10mA, V_R= 6V I_{rr}= 0.1 · I_R, R_L=100Ω			3	ns

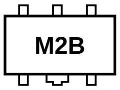
Note 1 : Rated input/output frequency : 100MHz
2 : * t_{rr} measuring circuit



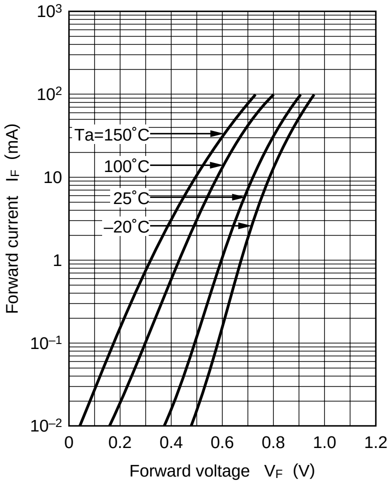




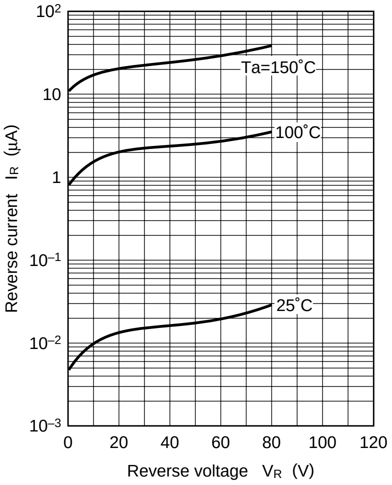
■ Marking



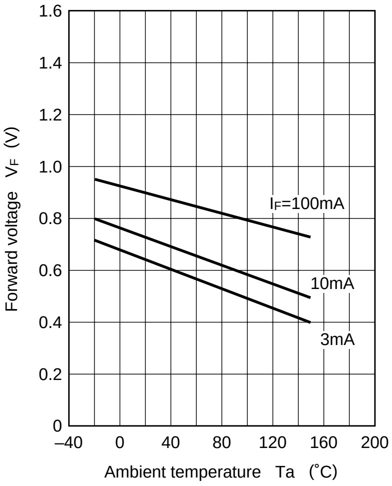
$I_F - V_F$



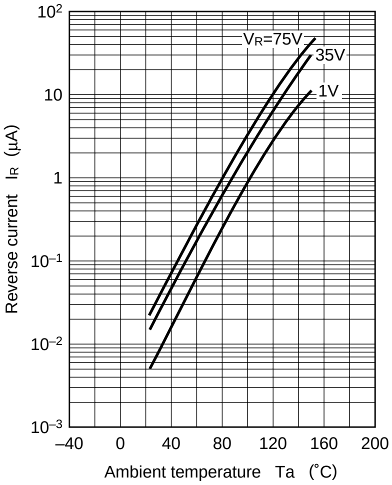
$I_R - V_R$



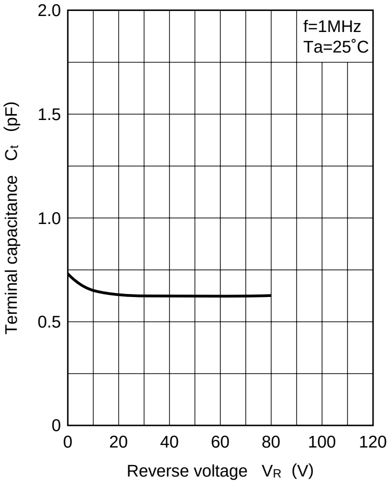
$V_F - Ta$



$I_R - Ta$



$C_t - V_R$



$I_{F\ (surge)} - t_W$